

PNP General Purpose Transistor

BCX17/BCX18

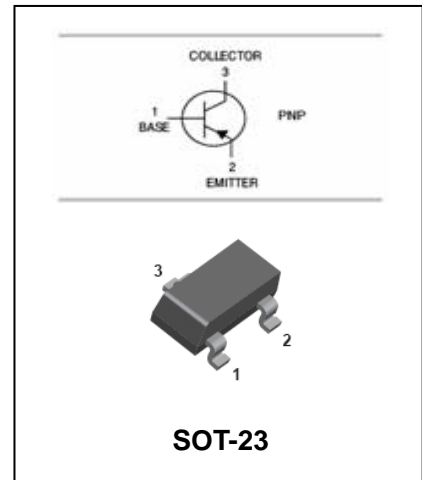
FEATURES

- High current (max.500mA).
- Low voltage(max.45V).



APPLICATIONS

- Saturated switching and driver applications e.g.for Industrial service.
- Thick and thin-film circuits



ORDERING INFORMATION

Type No.	Marking	Package Code
BCX17	T1	SOT-23
BCX18	T2	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	BCX17	-50
		BCX18	-30
V _{CEO}	Collector-Emitter Voltage	BCX17	-45
		BCX18	-25
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector current(DC)	-500	mA
I _{CM}	Peak collector current	-1	A
I _{BM}	Peak base current	-200	mA
P _{tot}	Total power dissipation	250	mW
R _{th j-a}	Thermal resistance from junction to ambient	500	K/W
T _j , T _{stg}	Junction and Storage Temperature	-65 to +150	°C



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$ BCX17 BCX18	-50 -30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$ BCX17 BCX18	-45 -25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-1V, I_C=-100mA$ $V_{CE}=-1V, I_C=-300mA$ $V_{CE}=-1V, I_C=-500mA$	100 70 40		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.62	V
Base-emitter on voltage	$V_{BE(on)}$	$I_C=-500mA, V_{CE}=-1V$			-1.2	V
Collector capacitance	C_C	$I_E=I_e=0, V_{CB}=-10V,$ $f=1MHz$		9		pF
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA$ $f=100MHz$	80			MHz

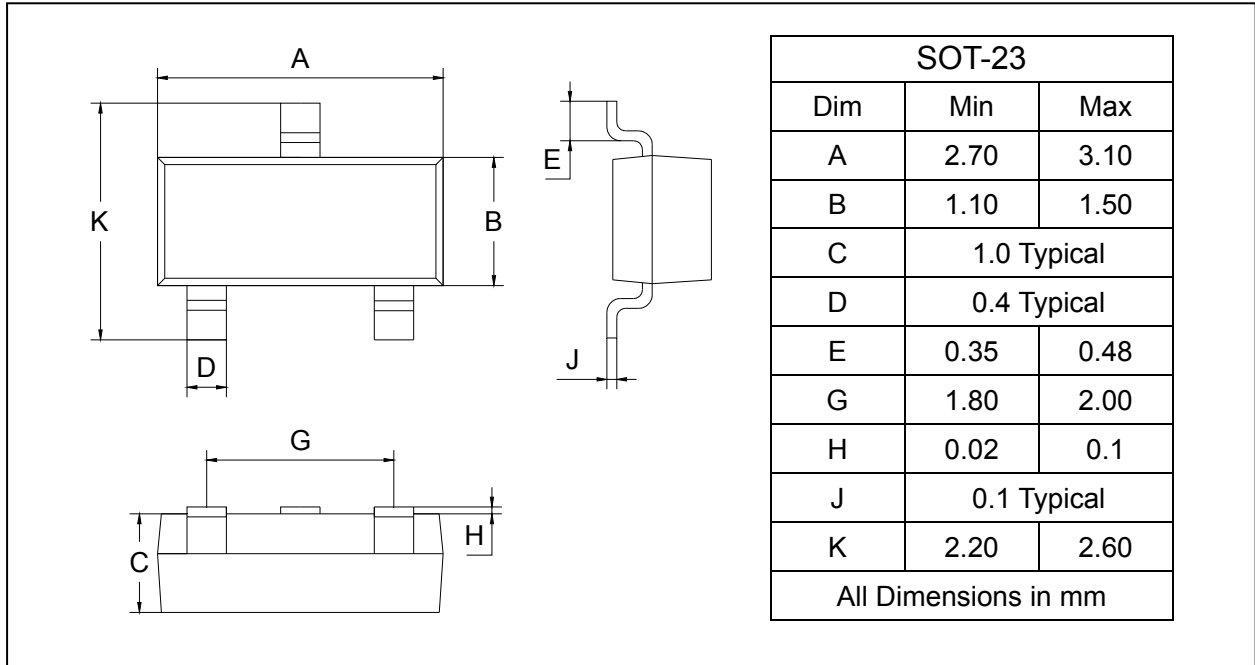
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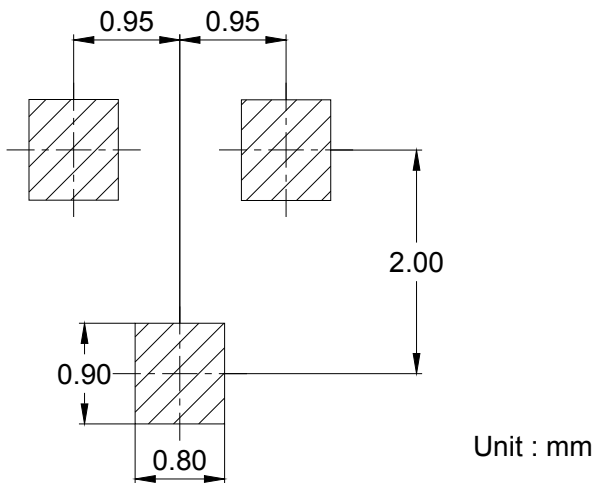
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BCX17/BCX18	SOT-23	3000/Tape&Reel